Transport through single molecules

Carsten Timm University of Kansas

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- Molecular electronics
- Transport theory
- Recent experiments

Theory: Tunneling through magnetic molecules

Kavli Institute for Theoretical Physics





# **Molecular electronics**



extrapolation: single molecules as transistors?

## **Molecular electronics**



## Also: possible self-assembly of components



## **Molecular electronics**



## Also: possible self-assembly of components



## **Molecular electronics**





Joachim *et al.*, Nature **408**, 541 (2000)

### Switches and memory

- deformations, change of conformation
- Iocal magnetic moments

### Readout (and writing)

require electronic tunneling through molecules

## **Mechanical break junction / electromigration**



 break junctions: bending of substrate

advantage: "reversible"

 electromigration: strong current, "fuse"

e.g., Reed et al., Science 278, 252 (1997)



### Weak coupling, sequential tunneling regime



1→2 L R

no current:

### Coulomb blockade

(like in quantum dots)



## Weak coupling, sequential tunneling regime





tunneling



### Weak coupling, sequential tunneling regime



local excitation  $1 \rightarrow 2$ 

### inelastic tunneling





### Weak coupling, cotunneling regime





### Weak coupling, cotunneling regime





- excitation far from chemical potentials (typical if no gate)
- virtual excitation

I / number of channels / Vbut small: I/V ;  $e^{2}/h$ 



### Weak coupling, cotunneling regime





inelastic tunneling opens new set of channels



### **Tunneling through single molecules: Mechanical break junction**



M.A. Reed, C. Zhou, C.J. Muller, T.P. Burgin, and J.M. Tour, Science **278**, 252 (1997)



steps in conductance

• symmetric & small  $(\ll e^2/h)$  conductance

 $\rightarrow$  cotunneling, no molecular excitations close to chemical potentials

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## **Coupling to vibrations:** C<sub>60</sub>

### contacts: electromigration

H. Park, J. Park, A.K.L. Lim, E.H. Anderson, A.P. Alivisatos, P.L. McEuen, Nature **407**, 57 (2000)







$$\frac{1}{7.0}$$

30 - 2

15

0

-15

-30

20

10

V (mV)

dI/dV

5.5

C



~ω ¼ 5 meV



### **Coupling to magnetic moment, Kondo effect**





dI/dV

0.4





## Anisotropic magnetic molecules: $Mn_{12}$ acetate

### contacts: electromigration

H. B. Heersche et al., PRL 96, 206801 (2006)





# Theory

## **Molecular electronics**

electronic manipulation of molecular charge, spin, conformation...:

## Inelastic transport through single molecules

### coupling to internal degrees of freedom, here: spin

- using magnetic molecules as memory devices:
  - write spin information electronically
  - store spin information
  - read spin information electronically



### Inelastic tunneling due to coupling to molecular spin

system: endohedral  $N@C_{60}$ nitrogen retains its spin  $S_N=3/2$  (Hund's 1<sup>st</sup> rule)  $C_{60}$  has 3-fold degenerate LUMO

$$H_{\mathrm{mol}} = \left(\epsilon_{\mathrm{LUMO}} - eV_g
ight) \hat{n} + rac{U}{2} \, \hat{n}(\hat{n}-1) - J \, \mathbf{S}_{\mathrm{C}_{60}} \cdot \mathbf{S}_{\mathrm{N}}$$

- $U\!\!:$  Hubbard repulsion on  $\mathrm{C}_{60}$
- J: ferromagnetic exchange

$$H_{\text{leads}} = \sum_{\alpha = \text{L,R}} \sum_{\mathbf{k}\sigma} \epsilon_{\mathbf{k}\sigma} a^{\dagger}_{\alpha\mathbf{k}\sigma} a_{\alpha\mathbf{k}\sigma}$$

$$H_{\rm t} = \sum_{\alpha = {\rm L}, {\rm R}} \sum_{n \mathbf{k}\sigma} (t_{\alpha} a^{\dagger}_{\alpha \mathbf{k}\sigma} c_{n\sigma} + t^{*}_{\alpha} c^{\dagger}_{n\sigma} a_{\alpha \mathbf{k}\sigma})$$

$$H = H_{\rm mol} + H_{\rm leads} + H_{\rm t}$$



Larson et al., J. Chem. Phys. 116, 7849 (2002)

production by ion implantation:

Almeida Murphy *et al.*, PRL **77**, 1075 (1996)



### **Density matrix formalism**

von Neumann equation for density matrix:

 $d\rho_I(t)/dt = -i[H_{tI}(t), \rho_I(t)]$ interaction rep.

$$\rho_I(t) = \rho_I(0) - i \int_0^t dt' \left[ H_{tI}(t'), \rho_I(t') \right]$$
teration:

$$d\rho_I(t)/dt = -i[H_{tI}(t), \rho_I(0)] - \int_0^t dt' [H_{tI}(t), [H_{tI}(t'), \rho_I(t')]]$$

reduced density matrix of molecule:

 $\rho_{\mathrm{mol}I}(t) \equiv \mathrm{Tr}_{\mathrm{leads}} \, \rho_I(t)$ 

Born approximation:

$$\rho_I(t) \approx \rho_{\text{mol}I}(t) \otimes \rho_{\text{leads}}^0$$

Markov approximation

 $\rho_{\mathrm{mol}I}(t') \approx \rho_{\mathrm{mol}I}(t)$ 

at this stage leads to perturbation theory of second order in tunneling

$$d\rho_{\rm mol}I(t)/dt \approx -\int_0^t dt' \operatorname{Tr}_{\rm leads}[H_{\rm t}I(t), [H_{\rm t}I(t'), \rho_{\rm mol}I(t) \otimes \rho_{\rm leads}^0]]$$

(sequential tunneling)



Back in Schrödinger picture:

$$d\rho_{\rm mol}(t)/dt \approx -i \left[H_{\rm mol}, \rho_{\rm mol}\right] - \operatorname{Tr}_{\rm leads} \int_0^\infty dt' \left[H_{\rm t}, \right]$$
$$\left[e^{-i(H_{\rm mol}+H_{\rm leads})t'} H_{\rm t} \, e^{i(H_{\rm mol}+H_{\rm leads})t'}, \rho_{\rm mol}(t) \otimes \rho_{\rm leads}^0\right]$$

cf. Mitra, Alleiner, and Millis, PRB 69, 245302 (2004).

Can evaluate this now. Alternative derivations:

diagrammatics on Keldysh time contour [König et al., PRB 54, 16820 (1996)]

 time-convolutionless master equation [Tokuyama and Mori, Prog. Theor. Phys. 54, 918 (1975)]

Assuming fast dephasing = rapid decay of off-diagonal components of  $\rho_{mol}$  obtain rate equations for probabilities  $P_n$  of molecular many-body states

$$\dot{P}_n = \sum_{m \neq n} P_m R_{m \to n} - P_n \sum_{m \neq n} R_{n \to m} \equiv \sum_m A_{nm} P_m$$

Stationary state:  $0 = \sum_{m} A_{nm} P_m$ 



### **Results for stationary state**

gate voltage

$$V_{\rm g}=0$$

temperature T = 0.01 K



F. Elste and C.T., PRB 71, 155403 (2005)



## **Differential conductance**



fine structure at temperature T = 0.1 K:

map of crossover points



# **Tunneling through magnetic molecules**

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Origin of fine structure:

- selection rules for single-electron tunneling
- occupation of initial state





### **Tunneling through molecule with magnetic anisotropy**





$$H_{\text{mol}} = (\epsilon - eV_g) \hat{n} + \frac{U}{2} \hat{n}(\hat{n} - 1) - J \mathbf{s} \cdot \mathbf{S} - K_2 (S^z)^2$$
anisotropy
anisotropy  $\rightarrow$  energy
barrier for spin reversal
C.T. and F. Elste,
PRB **73**, 235304 (2006)
$$K_2 = 0.04$$

$$n = 1$$

$$R = 0$$

$$R =$$



#### Relaxation of spin becomes slow





The only energetically allowed transitions from n = 0, m = 2 is to n = 1,  $m = 5/2 \rightarrow$  spin-down electron tunnels in (from right) then tunnels out (to left)





A spin-polarized current is flowing until the molecular spin relaxes (very slowly)



A macroscopic magnetic moment is transferred through the molecule

Here: relaxation due to thermal activation. Also possible due to spin tunneling from "up" to "down", see C. Romeike *et al.*, cond-mat/0511391

Macroscopic spin transfer is due to the small quantum spin  ${\bf S}$  of the molecule

Giant spin amplification

Possible read-out mechanism for molecular electronics





### Tunneling with one ferromagnetic and one nonmagnetic lead

C.T. and F. Elste, PRB **73**, 235304 (2006) F. Elste and C.T., PRB **73**, 235305 (2006)

can write the spin by applying a bias voltage (no magnetic field):





### Ferromagnetic/nonmagnetic leads: Spin blockade



vanishing anisotropy,  $K_2 = 0$ 



transition  $n = 1 \rightarrow 0, m \rightarrow m + 1/2$ (spin-down electron out) is suppressed by DOS in ferromagnetic lead







# **Conclusions**

### **Molecular electronics**



Inelastic transport through single molecules

Theory for magnetic molecules:

- coupling to spin: fine structure
- anisotropy: slow relaxation
- anisotropy: giant spin amplification
- one ferromagnetic lead: spin writing
- one ferromagnetic lead: spin blockade



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